

# **METHOD FOR AVOIDING POLYSILICON FILM OVER ETCH ABNORMAL**

## **ABSTRACT OF THE INVENTION**

5                   The method for avoiding polysilicon film over etch  
abnormal includes cleaning a semiconductor substrate. A  
dielectric layer is formed on the substrate. Subsequently, a  
10 first silicon source gas at a first flow rate is next performed  
injecting into a reaction chamber to form a first polysilicon film  
over the dielectric layer. Successively, a second silicon  
source gas at a second flow rate is performed injecting into the  
reaction chamber to form a second polysilicon film over the first  
15 polysilicon film, wherein the second silicon source gas having a  
different growth rate than the first silicon source gas. A  
patterned photoresist layer is then formed on the second  
polysilicon film. After the patterned photoresist layer is  
formed, a dry etching process by way of using the patterned  
20 photoresist layer as a etching mask is performed to etch  
through in turn the second polysilicon film and the first  
polysilicon film till exposing to the dielectric layer. Finally,  
the photoresist layer is removed.